

Title (en)
HALF-BRIDGE HAVING POWER SEMICONDUCTORS

Title (de)
HALBBRÜCKE MIT LEISTUNGSHALBLEITERN

Title (fr)
DEMI-PONT AYANT SEMI-CONDUCTEURS DE PUISSANCE

Publication
EP 3738200 A1 20201118 (DE)

Application
EP 18710367 A 20180227

Priority
EP 2018054788 W 20180227

Abstract (en)
[origin: WO2019166072A1] The invention relates to a half-bridge (102) comprising a first and second power semiconductor (108, 110, S1, S2, S3, S4) connected in series, a controller (120) for the power semiconductors (108, 110, S1, S2, S3, S4), a line which originates from the connecting node (112) of the power semiconductors (108, 110, S1, S2, S3, S4), an apparatus (130) for measuring the current in the line, wherein the controller (120) is configured to compare the current with an upper and a lower threshold value (132, 134), to switch off the first power semiconductor (108, 110, S1, S2, S3, S4) when the upper threshold value (132) is reached, and, following the expiry of a first dead time (210), to switch on the second power semiconductor (108, 110, S1, S2, S3, S4), and to switch off the second power semiconductor (108, 110, S1, S2, S3, S4) when the lower threshold value (134) is reached, and, following the expiry of a second dead time (212), to switch on the first power semiconductor (108, 110, S1, S2, S3, S4).

IPC 8 full level
H02M 1/38 (2007.01); **G05F 1/56** (2006.01); **H02M 1/00** (2006.01)

CPC (source: EP US)
H02M 1/38 (2013.01 - EP US); **H02M 1/0012** (2021.05 - EP US); **H02M 1/0058** (2021.05 - EP US); **H02M 1/0093** (2021.05 - EP US); **Y02B 70/10** (2013.01 - EP)

Citation (search report)
See references of WO 2019166072A1

Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)
BA ME

DOCDB simple family (publication)
WO 2019166072 A1 20190906; DE 112018007167 A5 20201210; EP 3738200 A1 20201118; US 11316423 B2 20220426; US 2021028690 A1 20210128

DOCDB simple family (application)
EP 2018054788 W 20180227; DE 112018007167 T 20180227; EP 18710367 A 20180227; US 201816975484 A 20180227